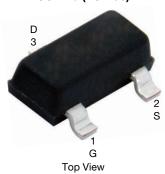


Vishay Siliconix

# Automotive P-Channel 12 V (D-S) 175 °C MOSFET

SOT-23 (TO-236)



Marking Code: 9T

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-12			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.050			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.068			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -1.8 \text{ V}$	0.100			
I <sub>D</sub> (A)	-5			
Configuration	Single			

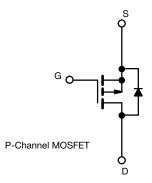
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2315CES (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> ( $T_C = 25$ °C, unles	s otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	-12	V
Gate-source voltage		$V_{GS}$	± 8	V
Continuous drain durrent	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	-5	
	T <sub>C</sub> = 125 °C		-3	
Continuous source current (diode conduction)		I <sub>S</sub>	-2.5	Α
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	-20	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-11	
Single pulse avalanche energy	L = 0.1 MH	E <sub>AS</sub>	6	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C	D	2	W
	T <sub>C</sub> = 125 °C	$P_{D}$	0.67	VV
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	R <sub>thJA</sub>	175	°C/W
Junction-to-foot (drain)		R <sub>thJF</sub>	75	G/W

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)

# Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							l
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	: 0 V, I <sub>D</sub> = -250 μA	-12	-	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.45	-	-1	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	= 0 V, V <sub>GS</sub> = ± 8 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -12 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -12 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -12 V, T <sub>J</sub> = 175 °C	1	-	-150	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -4.5 V	$V_{DS} \le -5 V$	-10	-	-	Α
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -3.5 A	-	0.042	0.050	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -3.5 A, T <sub>J</sub> = 125 °C	-	-	0.066	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -3.5 A, T <sub>J</sub> = 175 °C	-	-	0.075	Ω
		V <sub>GS</sub> = -2.5 V	I <sub>D</sub> = -3 A	-	0.059	0.068	1
		V <sub>GS</sub> = -1.8 V	I <sub>D</sub> = -2 A	-	0.084	0.100	•
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	$V_{DS} = -5 \text{ V}, I_{D} = -1.6 \text{ A}$		7	-	S
Dynamic <sup>b</sup>		<u> </u>					
Input capacitance	C <sub>iss</sub>			-	704	870	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -6 V, f = 1 MHz	-	276	335	рF
Reverse transfer capacitance	C <sub>rss</sub>			-	215	240	
Total gate charge c	Qg			-	9.3	13	
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V	$V_{DS} = -6 \text{ V}, I_{D} = -3.85 \text{ A}$	-	1.4	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	3.0	-	
Gate resistance	Rg		f = 1 MHz	2.4	4.9	12.3	Ω
Turn-on delay time c	t <sub>d(on)</sub>			-	11	26	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	= -6 V, R <sub>I</sub> = 1.6 Ω	-	27	30	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>		$V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	-	24	42	ns
Fall time °	t <sub>f</sub>	1			14	20	μA A Ω S pF
Source-Drain Diode Ratings and Chara	acteristics b	<u> </u>					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	-20	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	-2 A, V <sub>GS</sub> = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	22	44	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>-</sub> 1 2	A, di/dit = 100 A/μs	-	9	18	nC
Reverse recovery fall time	t <sub>a</sub>	ı <sub>+</sub> – -1.2	71, al/alt = 100 A/µ3	-	10	-	ns
Reverse recovery rise time	t <sub>b</sub>			-	12	-	
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-0.674	-	Α

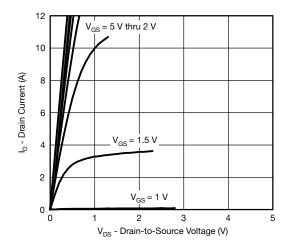
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

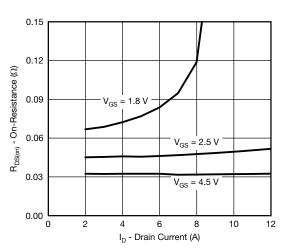
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



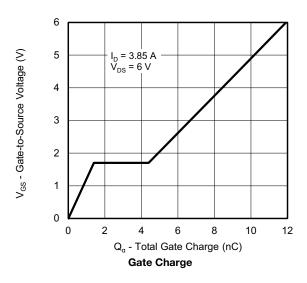
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

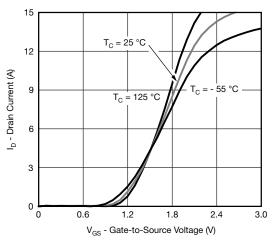


#### **Output Characteristics**

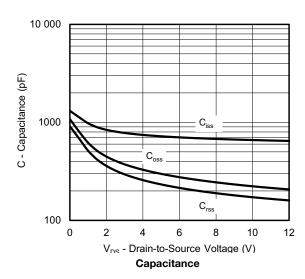


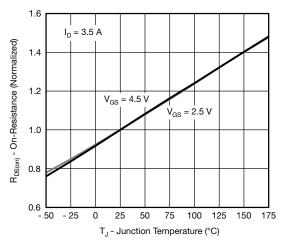
On-Resistance vs. Drain Current





**Transfer Characteristics** 

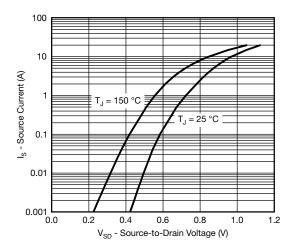




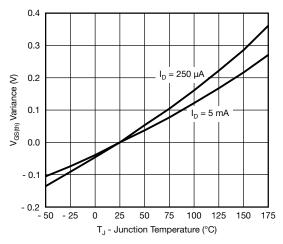
On-Resistance vs. Junction Temperature



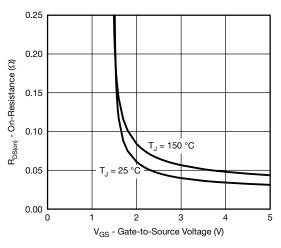
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



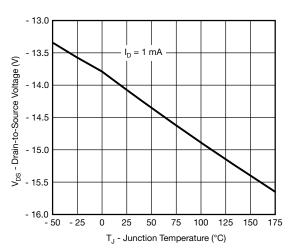
#### Source-Drain Diode Forward Voltage



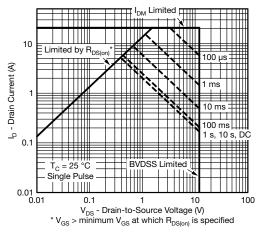
**Threshold Voltage** 



On-Resistance vs. Gate-to-Source Voltage



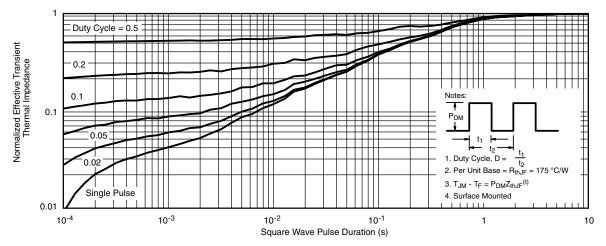
Drain Source Breakdown vs. Junction Temperature



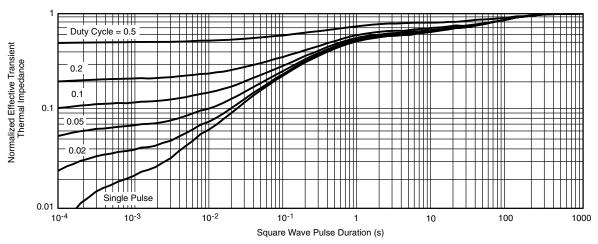
Safe Operating Area



### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

#### Note

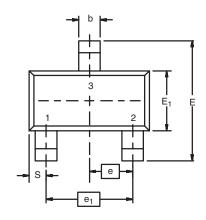
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

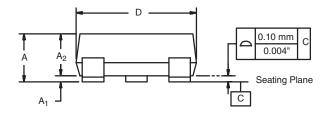
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

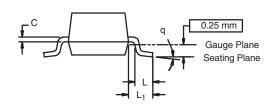
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62255">www.vishay.com/ppg?62255</a>.



# SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

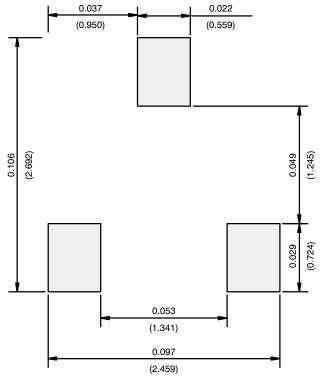
ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01 1



### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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